TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL MOS TYPE

# GT40M301

#### HIGH POWER SWITCHING APPLICATIONS

• The 3rd Generation

• FRD Included Between Emitter and Collector

• Enhancement-Mode

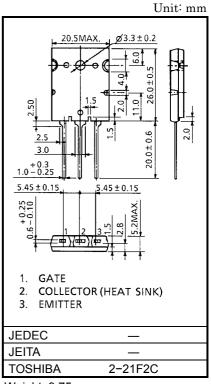
• High Speed IGBT :  $t_f = 0.25 \mu s$  (TYP.)

FRD :  $t_{rr} = 0.7 \mu s$  (TYP.)

• Low Saturation Voltage : VCE (sat) = 3.4V (MAX.)

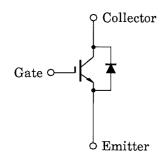
### **MAXIMUM RATINGS (Ta = 25°C)**

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V <sub>CES</sub>	900	V	
Gate-Emitter Voltage		V <sub>GES</sub>	±25	V	
Collector Current	DC	IC	40	Α	
	1ms	I <sub>CP</sub>	80	Α	
Emitter-Collector Foward Current	DC	I <sub>ECF</sub>	15	Α	
	1ms	I <sub>ECFP</sub>	120	Α	
Collector Power Dissipation (Tc = 25°C)		PC	200	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T <sub>stg</sub>	-55~150	°C	
Screw Torque		_	0.8	N·m	



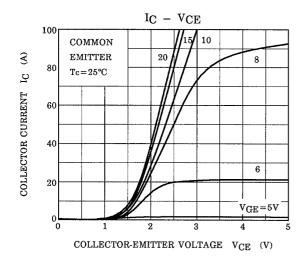
Weight: 9.75g

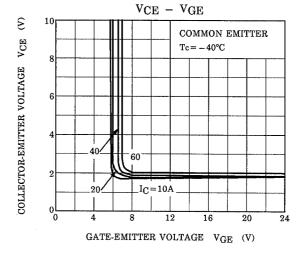
## **EQUIVALENT CIRCUIT**

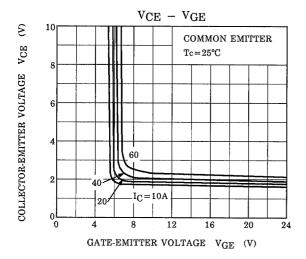


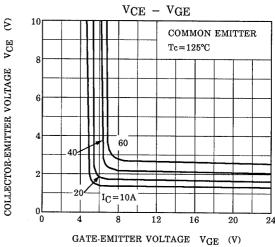
# **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

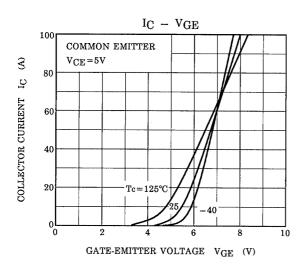
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I <sub>GES</sub>	V <sub>GE</sub> = ±25V, V <sub>CE</sub> = 0	_	_	±500	nA
Collector Cut-off Current		I <sub>CES</sub>	V <sub>CE</sub> = 900V, V <sub>GE</sub> = 0	_	_	1.0	mA
Gate-Emitter Cut-off Voltage		V <sub>GE</sub> (OFF)	I <sub>C</sub> = 40mA, V <sub>CE</sub> = 5V	3.0	_	6.0	V
Collector-Emitter Saturation Voltage		V <sub>CE</sub> (sat) (1)	I <sub>C</sub> = 8A, V <sub>GE</sub> = 15V	_	1.7	2.4	V
Collector-Emitter Saturation Voltage		V <sub>CE</sub> (sat) (2)	I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V	_	2.1	3.4	V
Input Capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0 f = 1MHz	_	2100	_	pF
Switching Time	Rise Time	t <sub>r</sub>	15V	_	0.30	0.60	- µs
	Turn-On Time	t <sub>on</sub>		_	0.40	0.70	
	Fall Time	t <sub>f</sub>		_	0.25	0.40	
	Turn-Off Time	t <sub>off</sub>		_	0.60	1.00	
Emitter-Collector Forward Voltage		V <sub>ECF</sub>	I <sub>EC</sub> = 15A, V <sub>GE</sub> = 0	_	1.5	2.0	V
Reverse Recovery Time		t <sub>rr</sub>	$I_F = 15A$ , $V_{GE} = 0$ , di / dt = -20A / $\mu$ s	_	0.7	2.5	μs
Thermal Resistance		R <sub>th (j-c)</sub>	IGBT	_	_	0.625	°C/W
Thermal Resistance		R <sub>th (j-c)</sub>	Diode	_	_	4.0	°C/W

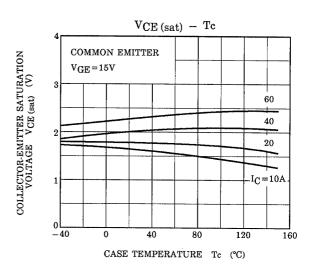


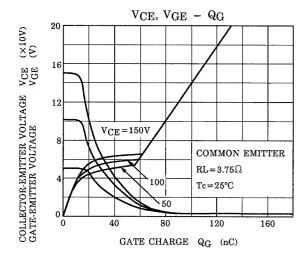


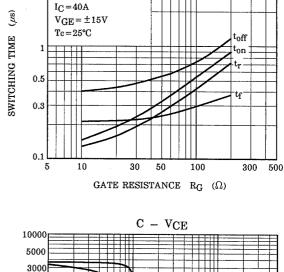






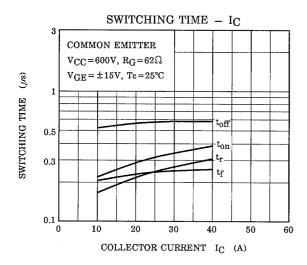


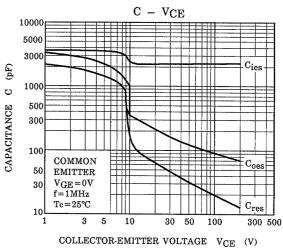


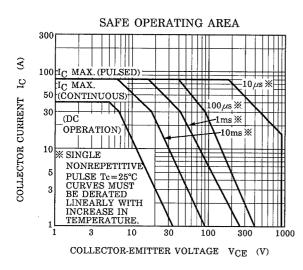


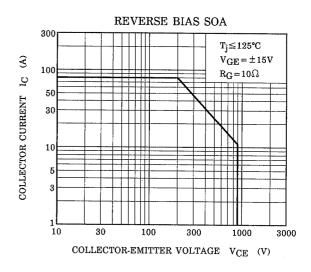
 $\begin{array}{l} \text{COMMON EMITTER} \\ V_{\text{CC}} \! = \! 600 \text{V} \end{array}$ 

SWITCHING TIME - RG

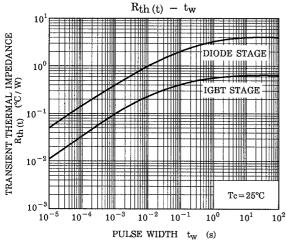


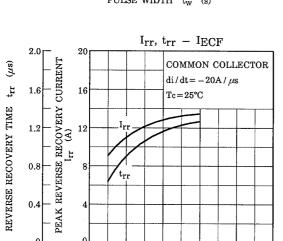






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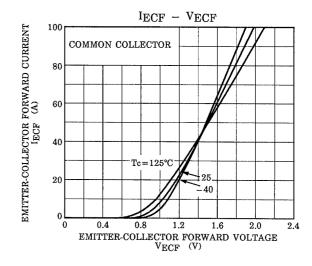
20

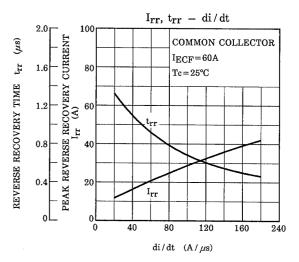
60

EMITTER-COLLECTOR FORWARD CURRENT IECF (A)

80

100





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